



WBFBP-02C Plastic-Encapsulate Diodes

DS751-40LED02 Schottky barrier Diode

DESCRIPTION

Silicon epitaxial planar

FEATURES

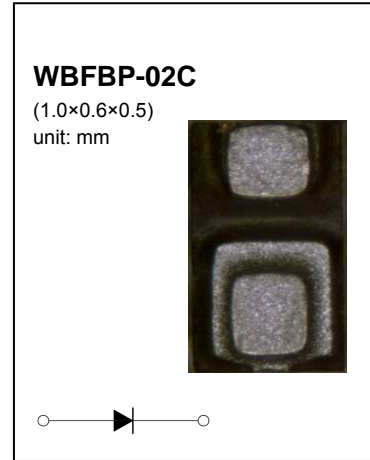
- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability

APPLICATION

High speed switching for detection

For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC, etc.)

MARKING: 5



Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	30	V
Mean rectifying current	I_O	30	mA
Peak forward surge current	I_{FSM}	150	mA
Power dissipation	P_D	100	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	1000	°C/W
Junction temperature	T_j	105	°C
Storage temperature	T_{stg}	-55~+150	°C

Electrical Ratings @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Forward voltage	V_F			0.37	V	$I_F=1mA$
Reverse current	I_R			0.5	μA	$V_R=30V$
Capacitance between terminals	C_T		2		pF	$V_R=1V, f=1MHZ$